

United States Patent and Trademark Office



W

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	NEY DOCKET NO. CONFIRMATION NO.	
09/318,159	05/25/1999	HOWARD E. RHODES	M4065.0335/P335-A	9990	
	7590 12/05/2003	EXAMINER			
THOMAS J. D'AMICO, ESQ.			MUNSON, GENE M		
DICKSTEIN, SHAPIRO, MORIN & OSHINSKY LLP			ART UNIT	PAPER NUMBER	
2101 L STREET. N.W. WASHINGTON DC 20037			2811		

DATE MAILED: 12/05/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

		A = = (1 4 11 11 11 1		<u>^ '</u>
!		Application No. 09/318, 159	Applicant(s)	RHODES	•
j [*]	Office Action Summary	Examiner G, Ma	INSON	Group Art Unit	
	-The MAILING DATE of this communication appears				 229
Perio	d for Reply			······································	
	ORTENED STATUTORY PERIOD FOR REPLY IS SET TO	EXPIRE THREE	MONTH(S) FROM THE MAILII	NG' DATE
fro - If - If - Fa - Ai	ctensions of time may be available under the provisions of 37 CFR 1. orn the mailing date of this communication. The period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, such period shall, by default, allure to reply within the set or extended period for reply will, by statury reply received by the Office later than three months after the mailing madjustment. See 37 CFR 1.704(b).	bly within the statutory min expire SIX (6) MONTHS fro te, cause the application to	mum of thirty (3 m the mailing da become ABAN	0) days will be considerentee of this communication	ed timely. on. 3).
Statu					
(23)	Responsive to communication(s) filed on	ember 2003			
X	This action is FINAL.				
	Since this application is in condition for allowance except faccordance with the practice under <i>Ex parte Quayle</i> , 1935	or formal matters, pro s C.D. 1 1; 453 O.G. 213.	ecution as to	o the merits is clos	ed in
Dispo	sition of Claims				
X	Claim(s) <u>45,46,50-52,54,56,59,60,</u>	2 is/are p	ending in the applica	tion.	
(Of the above claim(s)	is/are w	is/are withdrawn from consideration.		
図(Claim(s) 45,46,50-52,68,70	is/are al	is/are allowed.		
Ø	Claim(s) 54, 56, 73, 74, 77	is/are re	is/are rejected.		
3 (Claim(s) 59, 60	is/are of	is/are objected to.		
	Claim(s)				
	ation Papers The proposed drawing correction, filed on	is 🗆 approved (requiren ☐ disapprove		
	The drawing(s) filed on is/are objecte	d to by the Examiner			
□ 1	he specification is objected to by the Examiner.	·			
□ T	he oath or declaration is objected to by the Examiner.				
riorit	y under 35 U.S.C. § 119 (a)-(d)				
	cknowledgement is made of a claim for foreign priority un	der 35 U.S.C. § 119 (a)-	-(d).		
	All □ Some* □ None of the:				
ί	☐ Certified copies of the priority documents have been rec	eived.	•		
[☐ Certified copies of the priority documents have been rec	eived in Application No)	•	
(☐ Copies of the certified copies of the priority documents I	nave been received			
	in this national stage application from the International E		**		
*Cei	tified copies not received:				
ttach	ment(s)				
□ Ir	nformation Disclosure Statement(s), PTO-1449, Paper No(s) 🗆 Int	erview Summ	ary, PTO-413	
	otice of Reference(s) Cited, PTO-892	□ No	tice of Inform	al Patent Application	, PTO-152
	otice of Draftsperson's Patent Drawing Review, PTO-948			T	
	Office Assi	on Summary			
	Unice Acti	un sunimary			

U.S. Patent and Trademark Office PTO-326 (Rev. 11/00)

Part of Paper No. 4/

Art Unit: 2811

The process terminology (claim 73) is considered only in terms of a necessary *resultant* structure from the process. The process itself is not at issue. The device claims are *not* limited to the recited process. See MPEP 2113; *In re Brown*, 173 USPQ 685 (CCPA 1972); *In re Fitzgerald*, 205 USPQ 594 (CCPA 1980); *In re Marosi*, 218 USPQ 289, 292-293 (CCPA 1983); *In re Thorpe*, 227 USPQ 964 (Fed. Cir. 1985). In terms of *resultant structure*, the "ion implanted" region is taken as a region of N or P conductivity type.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 54, 56, 73, 74 and 77 are rejected under 35 U.S.C. 103 as unpatentable, the evidence being Schuegraf et al, Kooi et al and Joo et al, considered together. The "first" area and dielectric material reads on dielectric film 24 of Schuegraf et al (Figure 3D); the "second" area and dielectric material reads on different dielectric material 26. For a "field implant dose" as in Schuegraf et al (column 4, lines 32-36, "field threshold voltage is influenced by a number of physical and material properties of the trench isolator such as . . . substrate doping, field implant dose"), it would have been obvious to use a field implant region with a higher doping concentration similar to zone 6, 28 or 44 of Kooi et al (Figures 2, 10, 17), or layer 68 of Joo et al (Figure 15). Such an obvious field implant region would be a channel stop as in Joo et al. An "active" region reads on a

Art Unit: 2811

region adjacent a trench which is "displaced away from" a field implant doped region under trench dielectric 26 (claim 73). The "memory" device (claim 73) or "memory cell" (claim 77) reads on a typical DRAM application taught by Schuegraf et al (column 4).

In Schuegraf et al, the width of an isolation trench is approximately 250 nm (column 4, lines 23-26), the thickness of "first" area dielectric 24 is at least 5 nm (column 5, lines 12-15), so that the "first" area on both sides of trench 22 would be 10/250, which is less than 40 percent, of the width of the isolation trench, as in claim 73. At least "about" 100 angstroms (claim 56) is taken to encompass at least 50 angstroms. Alternatively, it would have been obvious to chose a thickness of dielectric material 24 to be "about" 100 angstroms, which is comparable and consistent to at least 50 angstroms (5 nm) suggested by Schuegraf et al. A field implant region below trench dielectric 26 is "displaced" from a surface "active" region adjacent to the trench 22 by at least a fraction of the depth of the trench (column 4, lines 23-26, 200 nm equals 2000 angstroms), which fraction would equal at least 100 angstroms, which is a distance "at least equal" to the thickness of "first" dielectric material 24, as in claim 73.

The impurity concentration of a field implant region establishes a "field threshold voltage" (claim 54) as noted by Schuegraf et al (column 4, lines 32-36, "field threshold voltage is influenced by a number of physical and material properties of the trench isolator such as . . . substrate doping, field implant dose"). The "first" dielectric material 24 is "on a bottom" of an "isolation" trench 22 (claim 74).

Art Unit: 2811

The conclusion is that the claimed invention as a whole would have been obvious at the time the invention was made to a person of ordinary skill in the art. The hypothetical person of ordinary skill in the art, familiar with all that Schuegraf et al, Kooi et al and Joo et al disclose, "would have found it obvious to make a structure corresponding to what is claimed." In re Sovish, 226 USPQ 771, 774 (Fed. Cir. 1985).

The references are of record.

The arguments in the response, filed 26 September 2003, have been considered but are not wholly persuasive, as noted above. Contrary to the response (pages 10-13), you cannot show non-obviousness by attacking references individually where, as here, the rejection is based on a combination of references. *In re Keller*, 208 USPQ 871, 882 (CCPA 1981). Contrary to the response (page 10), Kooi et al (Figures 2, 10, 17) and Joo et al (Figure 15) both do show an "isolation trench". Contrary to the response (pages 11-13), a "field implant dose" as in Schuegraf et al (column 4, lines 32-36, "field threshold voltage is influenced by a number of physical and material properties of the trench isolator such as . . . substrate doping, field implant dose") would have provided sufficient suggestion to use a field implant region with a higher doping concentration similar to zone 6, 28 or 44 of Kooi et al (Figures 2, 10, 17), or layer 68 of Joo et al (Figure 15).

Claims 45, 46, 50-52 and 68-70 are allowed over the art of record. Claims 59 and 60 are objected to as dependent upon a rejected claim but would be allowable if each were put in completed form as independent claims, including all limitations of claims 59, 73; 60, 73.

This action is FINAL.

Art Unit: 2811

This action is a final rejection and is intended to close the prosecution of this application.

Page 5

Applicant's reply under 37 CFR 1.113 to this action is limited either to an appeal to the Board of

Patent Appeals and Interferences or to an amendment complying with the requirements set forth

below.

If applicant should desire to appeal any rejection made by the examiner, a Notice of Appeal

must be filed within the period for reply identifying the rejected claim or claims appealed. The Notice

of Appeal must be accompanied by the required appeal fee of appropriate amount.

If applicant should desire to file an amendment, entry of a proposed amendment after final

rejection cannot be made as a matter of right unless it merely cancels claims or complies with a formal

requirement made earlier. Amendments touching the merits of the application which otherwise might

not be proper may be admitted upon a showing a good and sufficient reasons why they are necessary

and why they were not presented earlier.

A reply under 37 CFR 1.113 to a final rejection must include the appeal from, or cancellation

of, each rejected claim. The filing, whichever is longer, of an amendment after final rejection, whether

or not it is entered, does not stop the running of the statutory period for reply to the final rejection

unless the examiner holds the claims to be in condition for allowance. Accordingly, if a Notice of

Appeal has not been filed properly within the period for reply, or any extension of this period obtained

under either 37 CFR 1.136(a) or (b), the application will become abandoned.

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy

as set forth in 37 CFR 1.136(a).

Art Unit: 2811

A shortened statutory period for reply to this final action is set to expire THREE MONTHS

from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the

mailing date of this final action and the advisory action is not mailed until after the end of the

THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the

date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be

calculated from the mailing date of the advisory action. In no event, however, will the statutory

period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication should be directed to G. Munson at telephone

number (703) 308-4925 or 0956.

Munson

12/01/03

GENE M. MUNSON
EXAMINER
GROUP ART UNIT 2881

Page 6